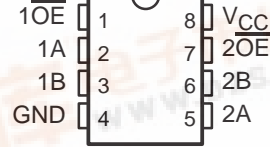


SN74CBTD3306 DUAL FET BUS SWITCH WITH LEVEL SHIFTING

SCDS030F – JANUARY 1996 – REVISED MAY 1998

- 5-Ω Switch Connection Between Two Ports
- TTL-Compatible Input Levels
- Designed to Be Used in Level-Shifting Applications
- Package Options Include Plastic Small-Outline (D) and Thin Shrink Small-Outline (PW) Packages

D OR PW PACKAGE
(TOP VIEW)



description

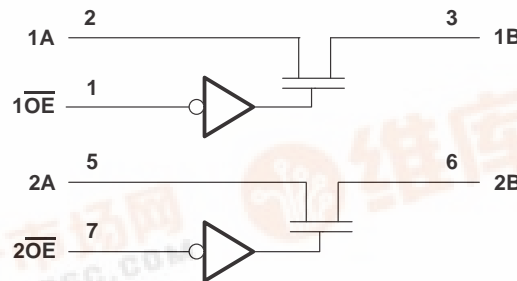
The SN74CBTD3306 features two independent line switches. Each switch is disabled when the associated output-enable (\overline{OE}) input is high. A diode to V_{CC} is integrated on the chip to allow for level shifting between 5-V inputs and 3.3-V outputs.

The SN74CBTD3306 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE
(each bus switch)

INPUT \overline{OE}	FUNCTION
L	A port = B port
H	Disconnect

logic diagram (positive logic)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SN74CBTD3306

DUAL FET BUS SWITCH WITH LEVEL SHIFTING

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 7 V
Input voltage range, V_I (see Note 1)	–0.5 V to 7 V
Continuous channel current	128 mA
Input clamp current, I_{IK} ($V_{I/O} < 0$)	–50 mA
Package thermal impedance, θ_{JA} (see Note 2): D package	197°C/W
PW package	243°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

	MIN	MAX	UNIT
V_{CC} Supply voltage	4.5	5.5	V
V_{IH} High-level control input voltage	2		V
V_{IL} Low-level control input voltage		0.8	V
T_A Operating free-air temperature	–40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP‡	MAX	UNIT	
V_{IK}	$V_{CC} = 4.5$ V,	$I_I = -18$ mA			–1.2	V	
V_{OH}	See Figure 2						
I_I	$V_{CC} = 5.5$ V,	$V_I = 5.5$ V or GND			±1	µA	
I_{CC}	$V_{CC} = 5.5$ V,	$I_O = 0$, $V_I = V_{CC}$ or GND			1.5	mA	
ΔI_{CC} §	Control inputs	$V_{CC} = 5.5$ V, One input at 3.4 V, Other inputs at V_{CC} or GND			2.5	mA	
C_i	Control inputs	$V_I = 3$ V or 0			3	pF	
$C_{io(OFF)}$	$V_O = 3$ V or 0,	$\overline{OE} = V_{CC}$			4	pF	
r_{on} ¶	$V_{CC} = 4.5$ V	$V_I = 0$	$I_I = 64$ mA		5	7	Ω
			$I_I = 30$ mA		5	7	
		$V_I = 2.4$ V,	$I_I = 15$ mA	35	50		

‡ All typical values are at $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

¶ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

SN74CBTD3306 DUAL FET BUS SWITCH WITH LEVEL SHIFTING

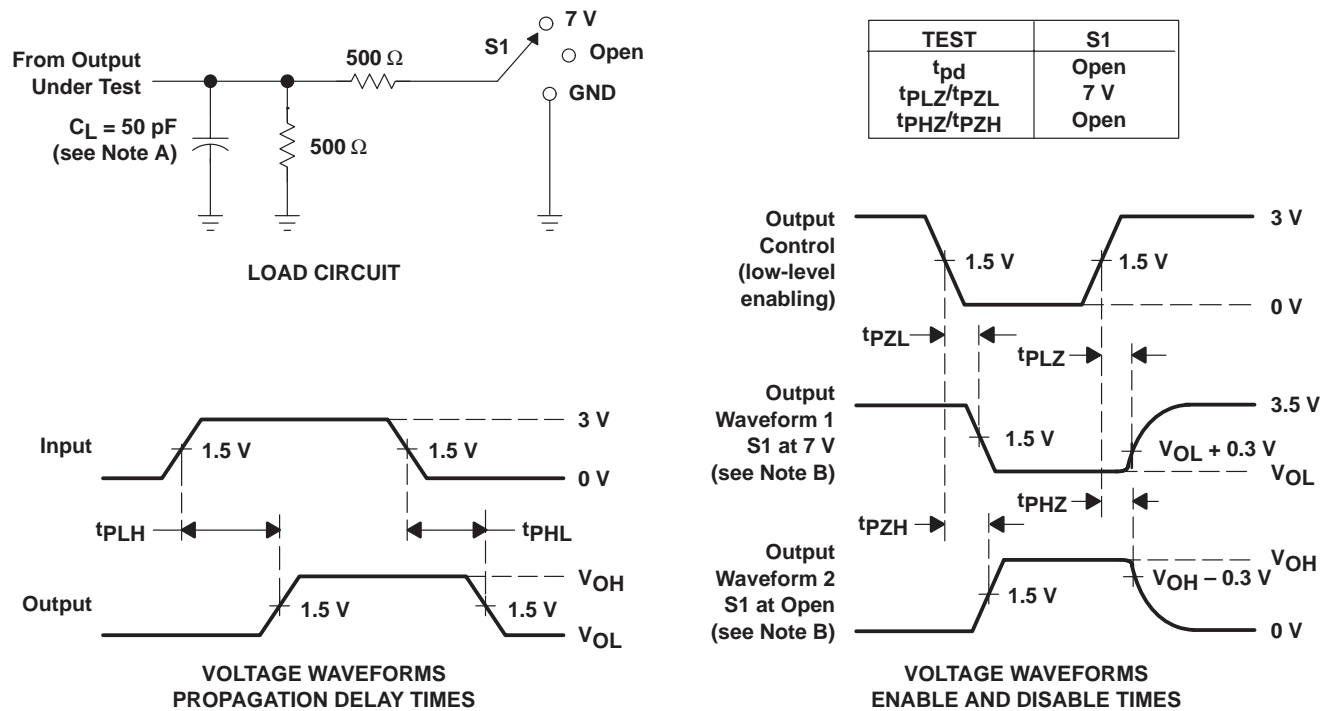
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switching characteristics over recommended ranges of supply voltage and operating free-air temperature range, $C_L = 50$ pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	MAX	UNIT
t_{pd}^\dagger	A or B	B or A		0.25	ns
t_{en}	\overline{OE}	A or B	2.1	5.4	ns
t_{dis}	\overline{OE}	A or B	1	4.7	ns

[†] The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

PARAMETER MEASUREMENT INFORMATION



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50$ Ω , $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PHL} and t_{PLH} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

SN74CBTD3306
DUAL FET BUS SWITCH
WITH LEVEL SHIFTING

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TYPICAL CHARACTERISTICS

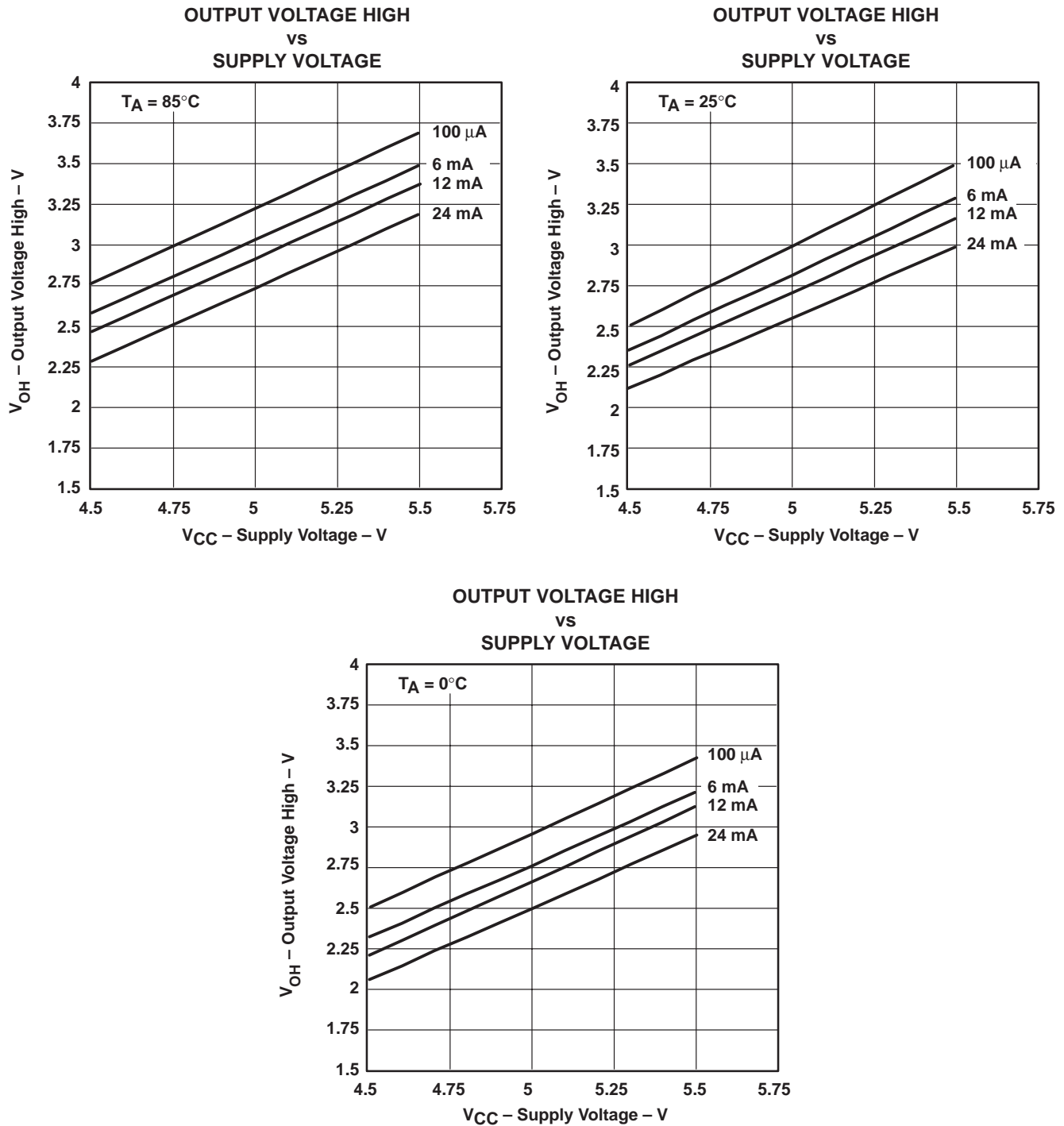


Figure 2. V_{OH} Values

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